J IvanÄ

List of Publications by Year
in descending order

64 papers	982 citations	471509 17 h-index	454955 30 g-index
65 all docs	65 docs citations	65 times ranked	998 citing authors

#	Article	IF	Citations
1	Acrylic acid nitrile, a film-forming electrolyte component for lithium-ion batteries, which belongs to the family of additives containing vinyl groups. Journal of Power Sources, 2003, 119-121, 368-372.	7.8	115
2	Reactivity of Au with ultrathin Si layers: A photoemission study. Journal of Applied Physics, 2001, 90, 345-350.	2.5	72
3	Sexithiophene films on ordered and disordered TiO2(110) surfaces: Electronic, structural and morphological properties. Surface Science, 2007, 601, 178-187.	1.9	64
4	Organic Heteroepitaxy:p-Sexiphenyl on Uniaxially Oriented Î±-Sexithiophene. Advanced Materials, 2006, 18, 2466-2470.	21.0	57
5	Substrate-Mediated Electronic Structure and Properties of Sexiphenyl Films. Advanced Materials, 2003, 15, 1812-1815.	21.0	48
6	Sexithiophene films on clean and oxidized Si(111) surfaces: Growth and electronic structure. Journal of Applied Physics, 2004, 96, 2716-2724.	2.5	41
7	The electronic band alignment on nanoscopically patterned substrates. Organic Electronics, 2007, 8, 63-68.	2.6	38
8	A disordered layered phase in thin films of sexithiophene. Chemical Physics Letters, 2013, 574, 51-55.	2.6	36
9	Î±-Sexithiophene on Cu(110) and Cu(110)â€"(2Ã—1)O: An STM and NEXAFS study. Surface Science, 2009, 603, 412-418.	1.9	32
10	Device relevant organic films and interfaces: A surface science approach. Surface Science, 2007, 601, 5683-5689.	1.9	30
11	Structure and morphology of sexiphenyl thin films grown on aluminium (111). Organic Electronics, 2004, 5, 45-51.	2.6	29
12	On validity of the Schottky-Mott rule in organic semiconductors: Sexithiophene on various substrates. Journal of Applied Physics, 2007, 101, 103712.	2.5	29
13	Epitaxial Growth of Sexiphenyl on Al(111):Â From Monolayer to Crystalline Films. Langmuir, 2004, 20, 7512-7516.	3.5	27
14	Methods of observation and elimination of semiconductor defect states. Solar Energy, 2006, 80, 645-652.	6.1	26
15	Ordered mono- and multilayer films of sexiphenyl on Al(111): a LEED investigation. Thin Solid Films, 2003, 433, 269-273.	1.8	25
16	Electronic and geometric structure of electro-optically active organic films and associated interfaces. Thin Solid Films, 2006, 514, 156-164.	1.8	25
17	Deoxidation of gallium arsenide surface via silicon overlayer: A study on the evolution of the interface state density. Journal of Applied Physics, 2005, 97, 073712.	2.5	20
18	Semiconductor surface and interface passivation by cyanide treatment. Applied Surface Science, 2004, 235, 279-292.	6.1	15

#	Article	IF	Citations
19	Oxygen induced molecular reorientation on aluminum. Applied Physics Letters, 2006, 88, 253111.	3.3	14
20	Au/GaAs(100) interface Schottky barrier modification by a silicon nitride intralayer. Journal of Applied Physics, 1997, 81, 292-296.	2.5	13
21	Elimination of interface states in the GaAs band-gap by cyanide treatment: XPS measurements under bias. Surface Science, 2003, 529, 329-337.	1.9	13
22	Epitaxial growth of sexithiophene on (110). Journal of Crystal Growth, 2008, 310, 101-109.	1.5	13
23	Towards new multifunctional coatings for organic photovoltaics. Solar Energy Materials and Solar Cells, 2014, 125, 127-132.	6.2	13
24	Nitric Dioxide and Acetone Sensors Based on Iron Oxide Nanoparticles. Sensor Letters, 2013, 11, 2322-2326.	0.4	12
25	Oxygen as a surfactant for Al contact metallization of organic layers. Applied Physics Letters, 2004, 85, 585-587.	3.3	11
26	Controlling geometric and electronic properties of highly ordered CuPc thin films. Applied Surface Science, 2009, 255, 6806-6808.	6.1	11
27	Intrinsic work function of molecular films. Thin Solid Films, 2012, 520, 3975-3986.	1.8	11
28	Critical evaluation of band bending determination in organic films from photoemission measurements. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1178-1182.	2.1	9
29	Tailoring the interparticle distance in Langmuir nanoparticle films. Physical Chemistry Chemical Physics, 2019, 21, 9553-9563.	2.8	9
30	Attempts to correlate hydrogen plasma-induced and Si3N4/GaAs interface-related surface states: a charge deep-level transient spectroscopy study. Applied Surface Science, 1997, 108, 187-196.	6.1	8
31	Unpinning of the Au/GaAs interfacial Fermi level by means of ultrathin undoped silicon interlayer inclusion. Journal of Applied Physics, 2000, 87, 795-800.	2.5	8
32	Metal/thin insulator/silicon schottky diodes with plasma deposited silicon nitride interfacial layer. Physica Status Solidi A, 1992, 130, 245-251.	1.7	7
33	Properties of metal-semiconductor contacts with plasma deposited silicon nitride interfacial layers. Journal of Crystal Growth, 1993, 126, 156-162.	1.5	7
34	Increased thermal stability of Au/GaAs metalâ€insulatorâ€semiconductor Schottky diodes with silicon nitride interfacial layer deposited by remote plasmaâ€enhanced chemical vapor deposition. Journal of Applied Physics, 1993, 73, 5075-5080.	2.5	7
35	Dissociation of sexithiophene on Al(111) surface. Organic Electronics, 2007, 8, 545-551.	2.6	7
36	Graphene Langmuir-Schaefer films Decorated by Pd Nanoparticles for NO₂ and H₂ Gas Sensors. Measurement Science Review, 2019, 19, 64-69.	1.0	7

#	Article	IF	Citations
37	Valence band fine structure of copper phthalocyanine thin films: Effect of molecular orientation. Physica Status Solidi (B): Basic Research, 2009, 246, 1510-1518.	1.5	6
38	Indium on a copper phthalocyanine thin film: Not a reactive system. Physical Review B, 2010, 81, .	3.2	6
39	Morphological and Electrical Properties of Stretched Nanoparticle Layers. Key Engineering Materials, 0, 644, 31-34.	0.4	6
40	Influence of plasma on silicon surface during lowâ€energy plasma deposition process: The comparative study on Si3N4/Si structures. Applied Physics Letters, 1994, 65, 2594-2596.	3.3	4
41	Electrical characterization of Au/SiOx/n-GaAs junctions. Solid-State Electronics, 1998, 42, 229-233.	1.4	4
42	Influence of the plasma pretreatment of GaAs(100) and Si(100) surfaces on the optical and structural properties of Si3N4/GaAs and a-SiGe/Si interfaces. Applied Surface Science, 2000, 166, 72-76.	6.1	4
43	A study of Al/Si3N4/ultrathin Si/GaAs structures by DLTS and Câ€“V measurements. Thin Solid Films, 2003, 433, 352-358.	1.8	4
44	Few-layer Graphene Langmuir-schaefer Nanofilms for H 2 Gas Sensing. Procedia Engineering, 2016, 168, 243-246.	1.2	4
45	Thermal stability of Î³-Fe₂O₃nanoparticles and their employment for sensing of acetone vapours. Journal of Physics: Conference Series, 2017, 939, 012009.	0.4	4
46	Cyclopean gauge factor of the strain-resistance transduction of indium oxide films. IOP Conference Series: Materials Science and Engineering, 2016, 108, 012043.	0.6	3
47	Correlation between electrical parameters and defect states of polythiophene:fullerene based solar cell. Thin Solid Films, 2016, 614, 16-24.	1.8	3
48	Response of alumina resistance to trace concentrations of acetone vapors at room temperature. Journal of Electrical Engineering, 2019, 70, 122-126.	0.7	3
49	A study on thermal emission of charges at Si3N4â€"GaAs interfaces after annealing in N2 and N2 + H2 mixtures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 40, 159-163.	3.5	2
50	Semi-insulating GaAs-based Schottky contacts in the role of detectors of ionising radiation: An effect of the interface treatment. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 434, 158-163.	1.6	2
51	Low-energy particle treatment of GaAs surface. Thin Solid Films, 2003, 433, 108-113.	1.8	2
52	Optical properties of sexithiophene films grown on ordered and disordered TiO2(110) surfaces. Thin Solid Films, 2008, 516, 4247-4251.	1.8	2
53	Towards organic solar cells without the hole transporting layer on the plasmonâ€enhanced ITO electrode. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 867-876.	1.8	2
54	Control of interparticle distance of ordered iron-oxide nanoparticle assemblies by means of surfactant design. AIP Conference Proceedings, 2018, , .	0.4	2

#	Article	IF	Citations
55	A marked change in electrical resistivity of alumina upon exposure to trace concentration of acetone vapours. Ceramics International, 2020, 46, 15876-15881.	4.8	2
56	On the accumulation capacitance of Si3N4/Si/GaAs structures fabricated in an electron cyclotron resonance plasma. Applied Surface Science, 1993, 72, 31-37.	6.1	1
57	Schottky barrier height dependence on the silicon interlayer thickness of AuSi-GaAs contacts : chemistry of interface formation study. Vacuum, 1998, 50, 407-411.	3.5	1
58	X-ray photoemission and photoreflectance study of Au/ultrathin Si/n-GaAs Schottky contacts and hydrogen plasma treated semi-insulating GaAs surfaces. Thin Solid Films, 1999, 343-344, 328-331.	1.8	1
59	Nitrogen Dioxide and Acetone Sensors Based on Iron Oxide Nanoparticles. Key Engineering Materials, 2014, 605, 318-321.	0.4	1
60	Sensitivity and long-term stability of γ-Fe<inf>2</inf>O<inf>3</inf> and CoFe<inf>2</inf>O<inf>4</inf> nanoparticle gas sensors for NO<inf>2</inf>, CO and acetone sensing — A comparative study. , 2014, , .		1
61	Colossal strain-resistance transduction of indium oxide films. Thin Solid Films, 2016, 616, 27-33.	1.8	1
62	An interpretation of dlts spectra of Al/Si3N4/ultrathin SI/GaAs structures â€" Effect of quantum well or interface states?. European Physical Journal D, 1993, 43, 875-879.	0.4	0
63	Gas sensing properties and electrical resistance of Langmuir-Blodgett iron oxide nanoparticle arrays. , 2012, , .		0
64	Graphene-based sensors of NO2, H2, acetone, and other gases/vapors: State of the art and realistic outlook. AIP Conference Proceedings, 2019, , .	0.4	0